

# Ting Wang

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/4607364/publications.pdf>

Version: 2024-02-01

74  
papers

2,014  
citations

331259

21  
h-index

233125

45  
g-index

74  
all docs

74  
docs citations

74  
times ranked

1783  
citing authors

| #  | ARTICLE                                                                                                                                                                                        | IF  | CITATIONS |
|----|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----|-----------|
| 1  | Ultrafast coherent control of a hole spin qubit in a germanium quantum dot. Nature Communications, 2022, 13, 206.                                                                              | 5.8 | 58        |
| 2  | Multi-wavelength 128 Gbit s <sup>-1</sup> PAM4 optical transmission enabled by a 100 GHz quantum dot mode-locked optical frequency comb. Journal Physics D: Applied Physics, 2022, 55, 144001. | 1.3 | 8         |
| 3  | Ultra-broadband flat-top quantum dot comb lasers. Photonics Research, 2022, 10, 1308.                                                                                                          | 3.4 | 22        |
| 4  | Gate-Tunable Spin-Orbit Coupling in a Germanium Hole Double Quantum Dot. Physical Review Applied, 2022, 17, .                                                                                  | 1.5 | 15        |
| 5  | Multi-wavelength injection locked semiconductor comb laser. Photonics Research, 2022, 10, 1840.                                                                                                | 3.4 | 13        |
| 6  | Hybrid Integration of Deterministic Quantum Dot-Based Single-Photon Sources with CMOS-Compatible Silicon Carbide Photonics. Laser and Photonics Reviews, 2022, 16, .                           | 4.4 | 11        |
| 7  | Epitaxial Growth of Ordered In-Plane Si and Ge Nanowires on Si (001). Nanomaterials, 2021, 11, 788.                                                                                            | 1.9 | 0         |
| 8  | Position-dependent chiral coupling between single quantum dots and cross waveguides. Applied Physics Letters, 2021, 118, .                                                                     | 1.5 | 17        |
| 9  | Anisotropic $g$ -Factor and Spin-Orbit Field in a Germanium Hut Wire Double Quantum Dot. Nano Letters, 2021, 21, 3835-3842.                                                                    | 4.5 | 16        |
| 10 | Sole Excited-State InAs Quantum Dot Laser on Silicon With Strong Feedback Resistance. Frontiers in Materials, 2021, 8, .                                                                       | 1.2 | 8         |
| 11 | Bufferless Epitaxial Growth of GaAs on Step-Free Ge (001) Mesa. Chinese Physics Letters, 2021, 38, 068101.                                                                                     | 1.3 | 3         |
| 12 | Chiral Photonic Circuits for Deterministic Spin Transfer. Laser and Photonics Reviews, 2021, 15, 2100009.                                                                                      | 4.4 | 8         |
| 13 | Suspended AlGaAs waveguide for integrated nonlinear photonics. Applied Physics Letters, 2021, 119, .                                                                                           | 1.5 | 3         |
| 14 | InAs/GaAs quantum dot single-section mode-locked lasers on Si (001) with optical self-injection feedback. Optics Express, 2021, 29, 674.                                                       | 1.7 | 27        |
| 15 | P-doped 1300 nm InAs/GaAs quantum dot lasers directly grown on an SOI substrate. Optics Letters, 2021, 46, 5525.                                                                               | 1.7 | 8         |
| 16 | Ultracompact Fiber-to-Chip Metamaterial Edge Coupler. ACS Photonics, 2021, 8, 3226-3233.                                                                                                       | 3.2 | 22        |
| 17 | 1300 nm and 1500 nm InAs/GaAs quantum dot lasers directly grown on SOI substrates for silicon photonics integration. , 2021, , .                                                               |     | 0         |
| 18 | O-band P-doped InAs/GaAs quantum dot lasers directly grown on SOI substrate. , 2021, , .                                                                                                       |     | 0         |

| #  | ARTICLE                                                                                                                                                            | IF   | CITATIONS |
|----|--------------------------------------------------------------------------------------------------------------------------------------------------------------------|------|-----------|
| 19 | Kerr nonlinearity induced four-wave mixing of CMOS-compatible PECVD deposited ultra-Si-rich-nitride. Journal of Applied Physics, 2020, 128, 013102.                | 1.1  | 4         |
| 20 | On-Chip Integration of Energy-Tunable Quantum Dot Based Single-Photon Sources via Strain Tuning of GaAs Waveguides. ACS Photonics, 2020, 7, 2723-2730.             | 3.2  | 12        |
| 21 | Nanowires: Site-Controlled Uniform Ge/Si Hut Wires with Electrically Tunable Spin-Orbit Coupling (Adv. Mater. 16/2020). Advanced Materials, 2020, 32, 2070122.     | 11.1 | 0         |
| 22 | Zero Field Splitting of Heavy-Hole States in Quantum Dots. Nano Letters, 2020, 20, 5201-5206.                                                                      | 4.5  | 12        |
| 23 | Site-Controlled Uniform Ge/Si Hut Wires with Electrically Tunable Spin-Orbit Coupling. Advanced Materials, 2020, 32, e1906523.                                     | 11.1 | 40        |
| 24 | A CMOS Compatible Si Template with (111) Facets for Direct Epitaxial Growth of III-V Materials*. Chinese Physics Letters, 2020, 37, 024203.                        | 1.3  | 11        |
| 25 | Hole spin in tunable Ge hut wire double quantum dot. Applied Physics Express, 2020, 13, 065002.                                                                    | 1.1  | 9         |
| 26 | Dipole coupling of a hole double quantum dot in germanium hut wire to a microwave resonator. New Journal of Physics, 2020, 22, 083068.                             | 1.2  | 14        |
| 27 | InAs/GaAs quantum dot narrow ridge lasers epitaxially grown on SOI substrates for silicon photonic integration. Optics Express, 2020, 28, 26555.                   | 1.7  | 32        |
| 28 | Phosphorus-free 1.5-µm InAs quantum-dot microdisk lasers on metamorphic InGaAs/SOI platform. Optics Letters, 2020, 45, 2042.                                       | 1.7  | 21        |
| 29 | Epitaxial growth of InAs/GaAs quantum dots on {113}-faceted Ge/Si (001) hollow substrate. Optical Materials Express, 2020, 10, 1045.                               | 1.6  | 6         |
| 30 | Controllable growth of GeSi nanowires on trench patterned Si(001) substrate. Wuli Xuebao/Acta Physica Sinica, 2020, 69, 028102.                                    | 0.2  | 3         |
| 31 | Telecom InAs quantum-dot FP and microdisk lasers epitaxially grown on (111)-faceted SOI. , 2020, , .                                                               |      | 0         |
| 32 | Perspective: optically-pumped III-V quantum dot microcavity lasers via CMOS compatible patterned Si (001) substrates. Journal of Semiconductors, 2019, 40, 101303. | 2.0  | 16        |
| 33 | InAs QDs Monolithically Grown on COMS Compatible Si (001) and SOI Platform with Strong Emission at 1300 nm and 1550 nm. , 2019, , .                                |      | 0         |
| 34 | O-Band and C/L-Band III-V Quantum Dot Lasers Monolithically Grown on Ge and Si Substrate. Applied Sciences (Switzerland), 2019, 9, 385.                            | 1.3  | 26        |
| 35 | Enhanced optical Kerr nonlinearity of graphene/Si hybrid waveguide. Applied Physics Letters, 2019, 114, .                                                          | 1.5  | 50        |
| 36 | O-band InAs/GaAs quantum-dot microcavity laser on Si (001) hollow substrate by in-situ hybrid epitaxy. AIP Advances, 2019, 9, 015331.                              | 0.6  | 14        |

| #  | ARTICLE                                                                                                                                      | IF  | CITATIONS |
|----|----------------------------------------------------------------------------------------------------------------------------------------------|-----|-----------|
| 37 | Optical Kerr Nonlinearity of CMOS Compatible PECVD Deposited Si-Rich-Nitride (SRN). , 2019, , .                                              |     | 0         |
| 38 | InAs QDs Monolithically Grown on COMS Compatible Si (001) and SOI Platform with Strong Emission at 1300 nm and 1550 nm. , 2019, , .          |     | 0         |
| 39 | Spectral Broadening Enhancement in Graphene Integrated Si Waveguides. , 2019, , .                                                            |     | 0         |
| 40 | Optical Kerr Nonlinearity of CMOS Compatible PECVD Deposited Si-Rich-Nitride (SRN). , 2019, , .                                              |     | 0         |
| 41 | 1310 nm InAs quantum-dot microdisk lasers on SOI by hybrid epitaxy. Optics Express, 2019, 27, 19348.                                         | 1.7 | 18        |
| 42 | Coupling a Germanium Hut Wire Hole Quantum Dot to a Superconducting Microwave Resonator. Nano Letters, 2018, 18, 2091-2097.                  | 4.5 | 36        |
| 43 | Enhanced optical Kerr nonlinearity of graphene/Si hybrid waveguide. , 2018, , .                                                              |     | 0         |
| 44 | InAs QDs on (111)-faceted Si (001) hollow substrates with strong emission at 1300 nm and 1550 nm. , 2018, , .                                |     | 0         |
| 45 | Optically pumped low threshold InAs/GaAs quantum-dot micropillar laser on Si (001) hollow substrate. , 2018, , .                             |     | 0         |
| 46 | A germanium hole spin qubit. Nature Communications, 2018, 9, 3902.                                                                           | 5.8 | 170       |
| 47 | Catalyst-free growth of lateral InAs nanowires. Journal of Crystal Growth, 2018, 498, 209-213.                                               | 0.7 | 1         |
| 48 | InAs QDs on (111)-faceted Si (001) hollow substrates with strong emission at 1300nm and 1550nm. Applied Physics Letters, 2018, 113, .        | 1.5 | 48        |
| 49 | Measuring the complex admittance and tunneling rate of a germanium hut wire hole quantum dot. Journal of Applied Physics, 2018, 123, 174305. | 1.1 | 3         |
| 50 | C/L-band InAs QDs on CMOS compatible Ge and on- axis Si (001) platform. , 2018, , .                                                          |     | 0         |
| 51 | Enhanced Self-Phase Modulation in Graphene-integrated Silicon Waveguides. , 2018, , .                                                        |     | 0         |
| 52 | O-band and C/L-band emission of InAs QDs monolithically grown on Ge and U-shape Si (001) platform. , 2018, , .                               |     | 0         |
| 53 | High gain optical parametric amplification in ultra-silicon-rich nitride (USRN) waveguides. , 2018, , .                                      |     | 0         |
| 54 | Measuring hole spin states of single quantum dot in germanium hut wire. Applied Physics Letters, 2017, 110, .                                | 1.5 | 19        |

| #  | ARTICLE                                                                                                                                                                                                                                              | IF   | CITATIONS |
|----|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|------|-----------|
| 55 | C/L-band emission of InAs QDs monolithically grown on Ge substrate. <i>Optical Materials Express</i> , 2017, 7, 2955.                                                                                                                                | 1.6  | 12        |
| 56 | C/L-band emission of InAs QDs monolithically grown on Ge platform. , 2017, , .                                                                                                                                                                       |      | 0         |
| 57 | Temperature-Dependent Photoluminescence Characteristics of InAs/GaAs Quantum Dots Directly Grown on Si Substrates. <i>Chinese Physics Letters</i> , 2016, 33, 044207.                                                                                | 1.3  | 4         |
| 58 | Supercontinuum generation in bandgap engineered, backâ€end CMOS compatible silicon rich nitride waveguides. <i>Laser and Photonics Reviews</i> , 2015, 9, 498-506.                                                                                   | 4.4  | 115       |
| 59 | Wavelength selective mode division multiplexing on a silicon chip. <i>Optics Express</i> , 2015, 23, 8095.                                                                                                                                           | 1.7  | 40        |
| 60 | Exploring High Refractive Index Silicon-Rich Nitride Films by Low-Temperature Inductively Coupled Plasma Chemical Vapor Deposition and Applications for Integrated Waveguides. <i>ACS Applied Materials &amp; Interfaces</i> , 2015, 7, 21884-21889. | 4.0  | 74        |
| 61 | Quantum dot lasers on silicon substrate for silicon photonic integration and their prospect. <i>Wuli Xuebao/Acta Physica Sinica</i> , 2015, 64, 204209.                                                                                              | 0.2  | 7         |
| 62 | Systematic z-scan measurements of the third order nonlinearity of chalcogenide glasses. <i>Optical Materials Express</i> , 2014, 4, 1011.                                                                                                            | 1.6  | 160       |
| 63 | Optical nonlinearity in silicon at mid-infrared wavelengths. , 2014, , .                                                                                                                                                                             |      | 0         |
| 64 | Second and third order dispersion generation using nonlinearly chirped silicon waveguide gratings. <i>Optics Express</i> , 2013, 21, 29223.                                                                                                          | 1.7  | 26        |
| 65 | Multi-photon absorption and third-order nonlinearity in silicon at mid-infrared wavelengths. <i>Optics Express</i> , 2013, 21, 32192.                                                                                                                | 1.7  | 103       |
| 66 | IIIâ€V quantum-dot laser growth on silicon and germanium. , 2013, , .                                                                                                                                                                                |      | 0         |
| 67 | 1300 nm Wavelength InAs Quantum Dot Photodetector Grown on Silicon. <i>Optics Express</i> , 2012, 20, 10446.                                                                                                                                         | 1.7  | 31        |
| 68 | 1.3-Î¼m InAs/GaAs quantum-dot lasers monolithically grown on Si substrates. <i>Optics Express</i> , 2011, 19, 11381.                                                                                                                                 | 1.7  | 236       |
| 69 | Long-wavelength InAs/GaAs quantum-dot laser diode monolithically grown on Ge substrate. <i>Nature Photonics</i> , 2011, 5, 416-419.                                                                                                                  | 15.6 | 344       |
| 70 | 1.3-um InAs/GaAs quantum-dot lasers monolithically grown on Ge substrate. , 2011, , .                                                                                                                                                                |      | 0         |
| 71 | Anisotropy of domain broadening in periodically poled lithium niobate crystals. <i>Applied Physics Letters</i> , 2006, 88, 041121.                                                                                                                   | 1.5  | 21        |
| 72 | Quasiphase matched harmonic generation in a two-dimensional octagonal photonic superlattice. <i>Applied Physics Letters</i> , 2005, 87, 251103.                                                                                                      | 1.5  | 37        |

| #  | ARTICLE                                                                                                                                       | IF  | CITATIONS |
|----|-----------------------------------------------------------------------------------------------------------------------------------------------|-----|-----------|
| 73 | Magnetic transport measurements of spin-orbit and hyperfine interactions in a Ge hut wire double quantum dot. Applied Physics Express, 0, , . | 1.1 | 0         |
| 74 | Ultra-silicon-rich nitride devices for CMOS nonlinear optics. SPIE Newsroom, 0, , .                                                           | 0.1 | 0         |